

/ Descriptions

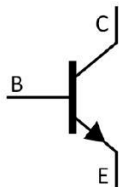
WR0459 QSQ Silicon NPN transistor in a TO-18 Plastic Package.

/ Features

EG56;
Complementary pair with BD238.

/ Applications

Medium power linear and switching applications.

/ Equivalent Circuit

PIN1 Emitter PIN 2 Collector PIN 3 Base

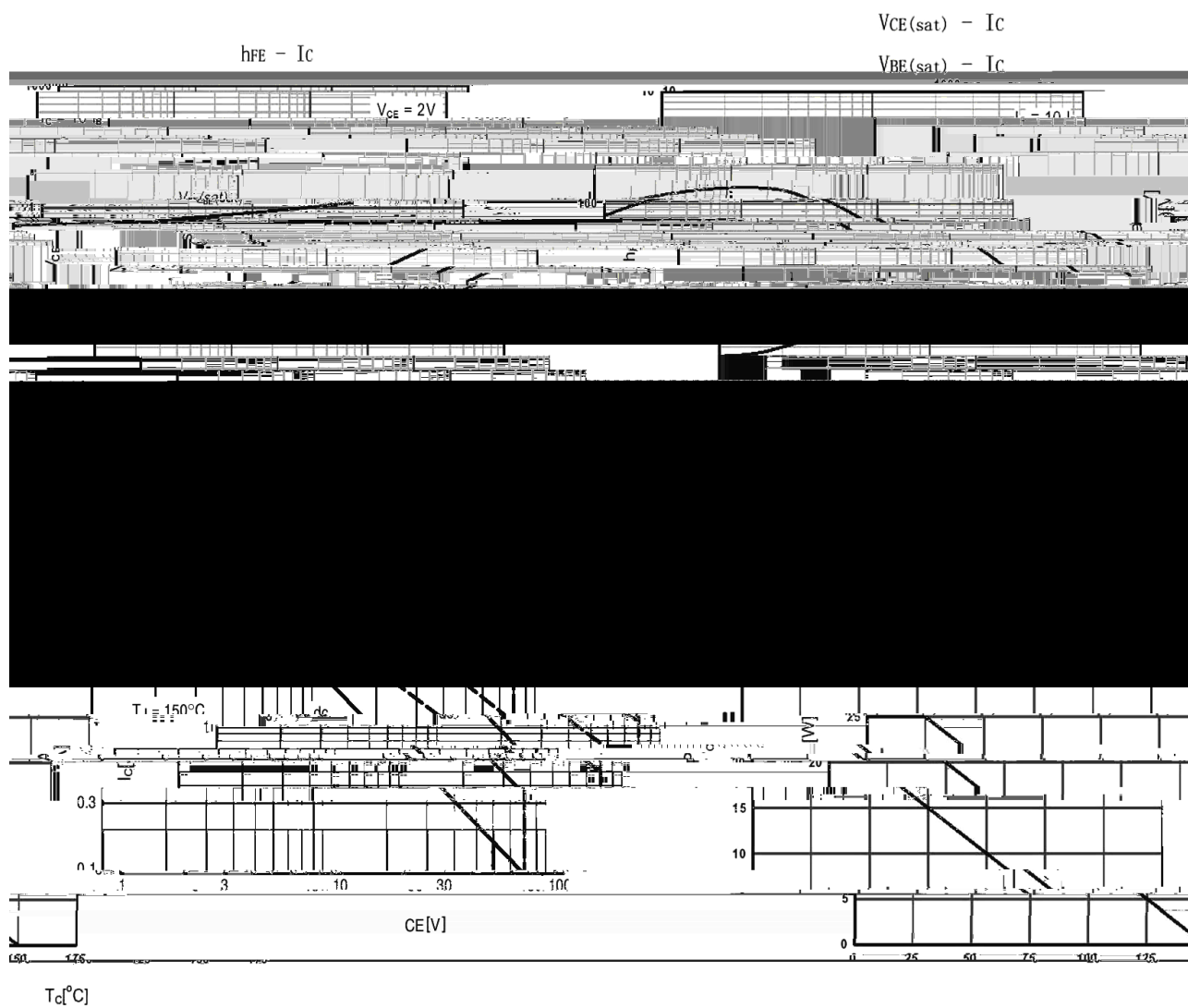
/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	2.0	A
Peak Collector Current	I_{CM}	6.0	A
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	25	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Á	°	>
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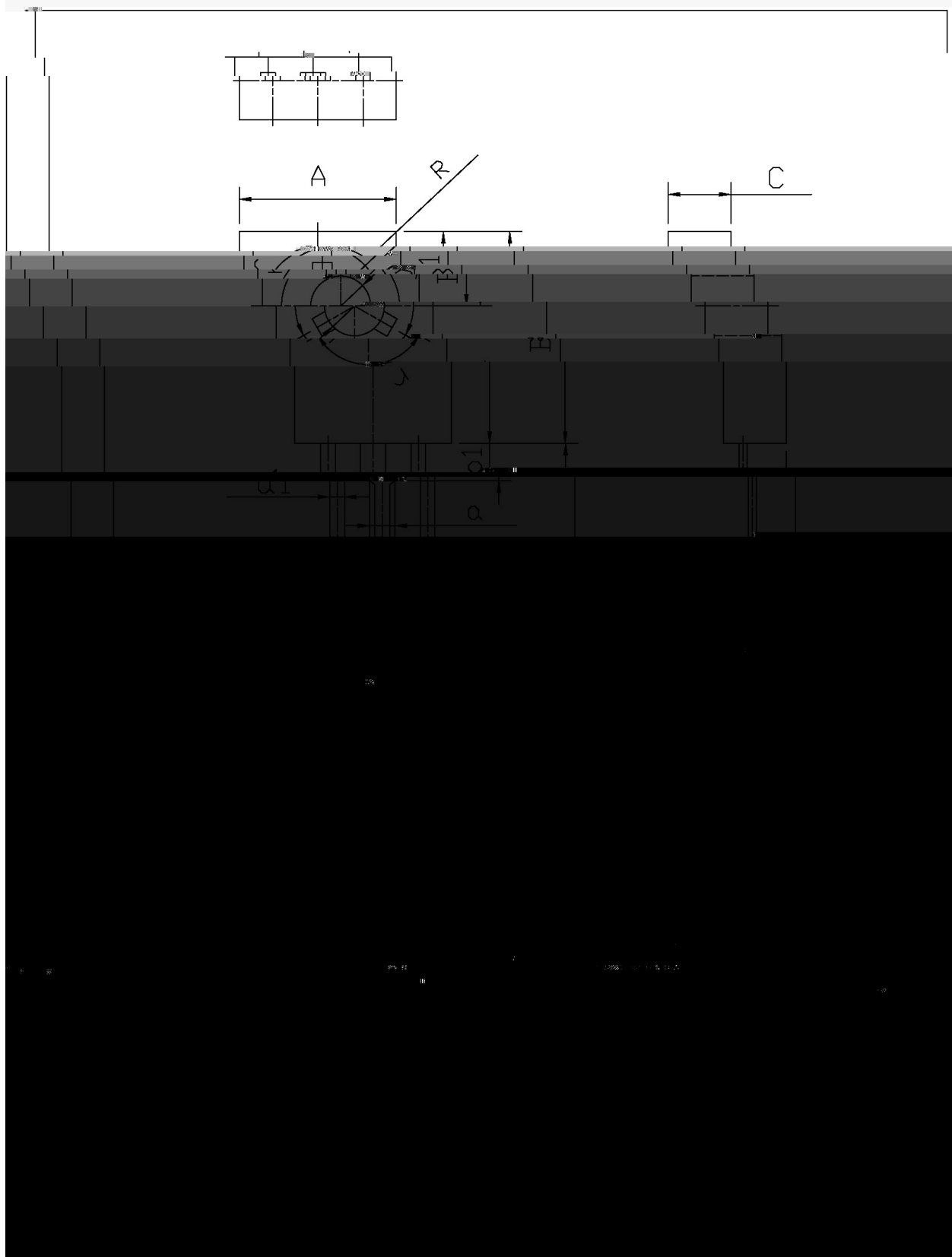
/ Electrical Characteristic Curve



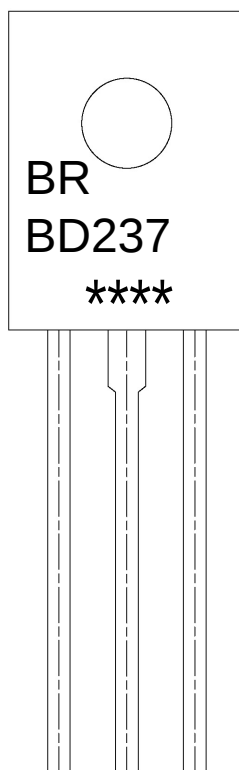
/ Package Dimensions

T□-126

单位: mm



/ Marking Instructions



EU

EG56 :

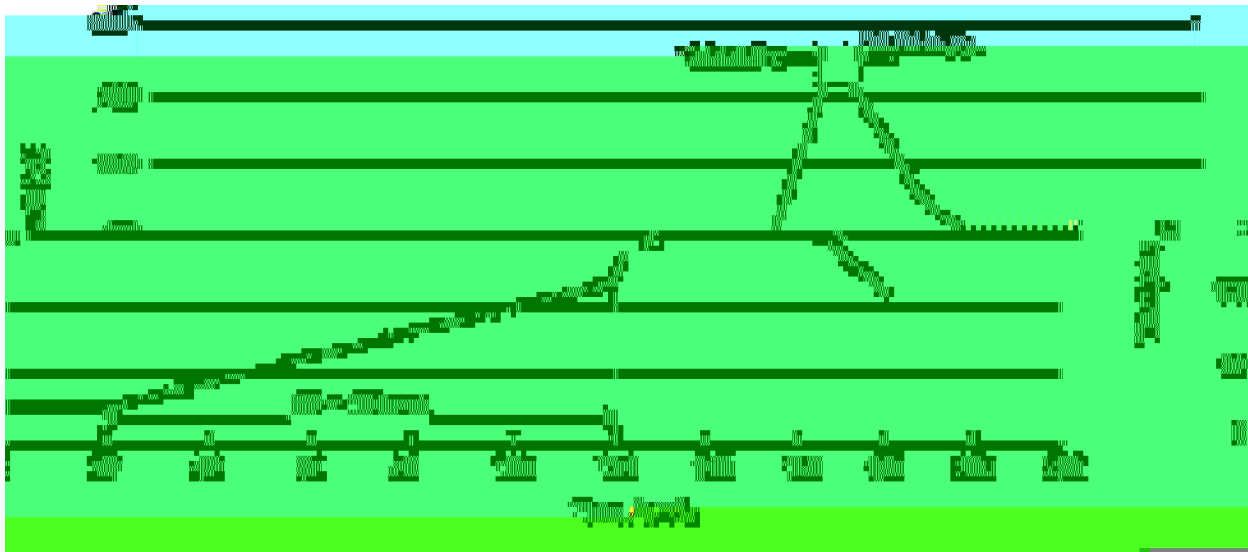
Note:

BR: Company Code

BD237: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note: